

FIG. 1 is a schematic diagram of a semiconductor device 100. The device includes a central channel 32, which is divided into three sub-regions: 32a, 32b, and 32c. On the left side of the channel are source regions 25 and 26, and on the right side are drain regions 42 and 43. A gate structure 34 is positioned above the channel. The device is bounded by a frame 33, which includes a central section 33c and side sections 33a and 33b. Various other components are labeled with numbers 9, 17, 23, 44, 45, and 41. Arrows D and E indicate directions.

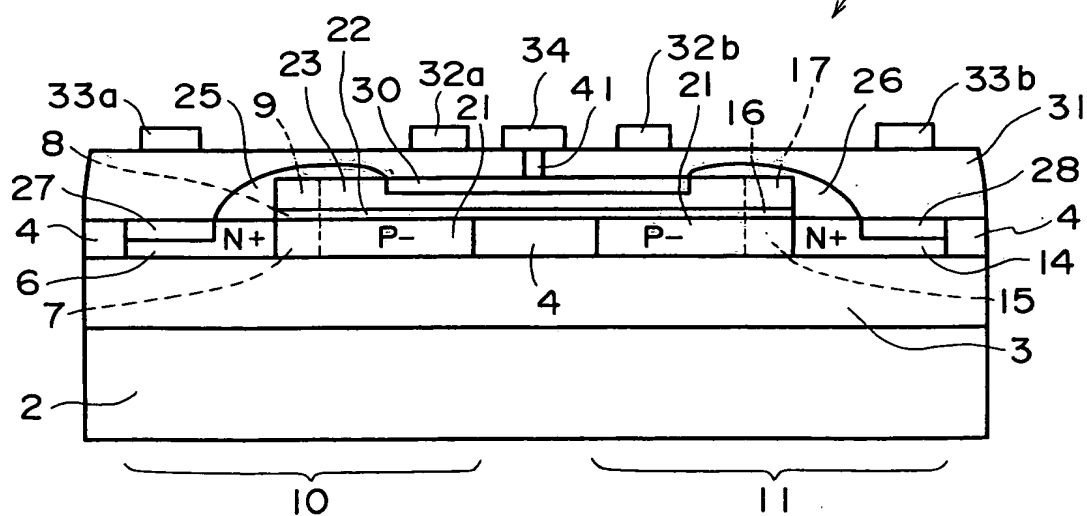
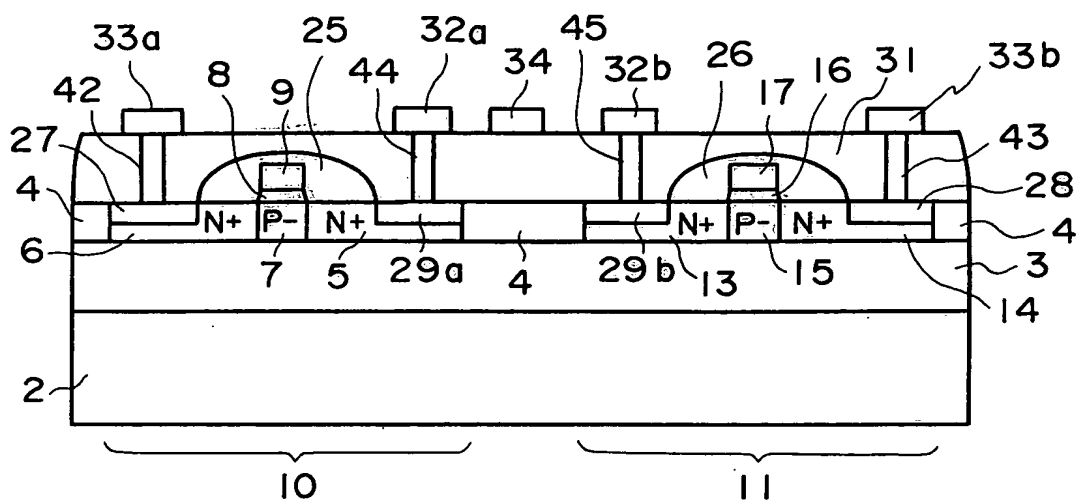


FIG. 3

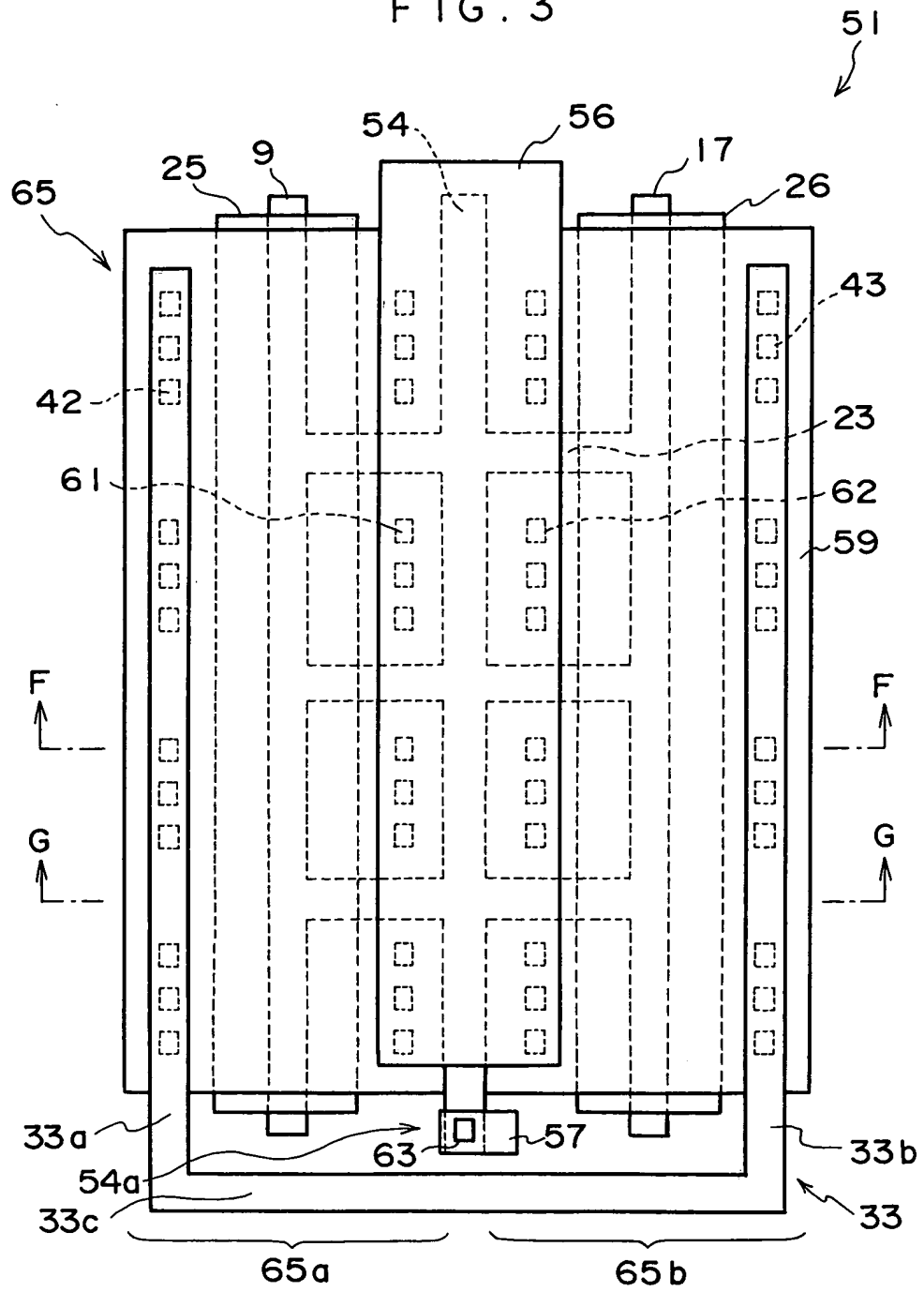


FIG. 4A

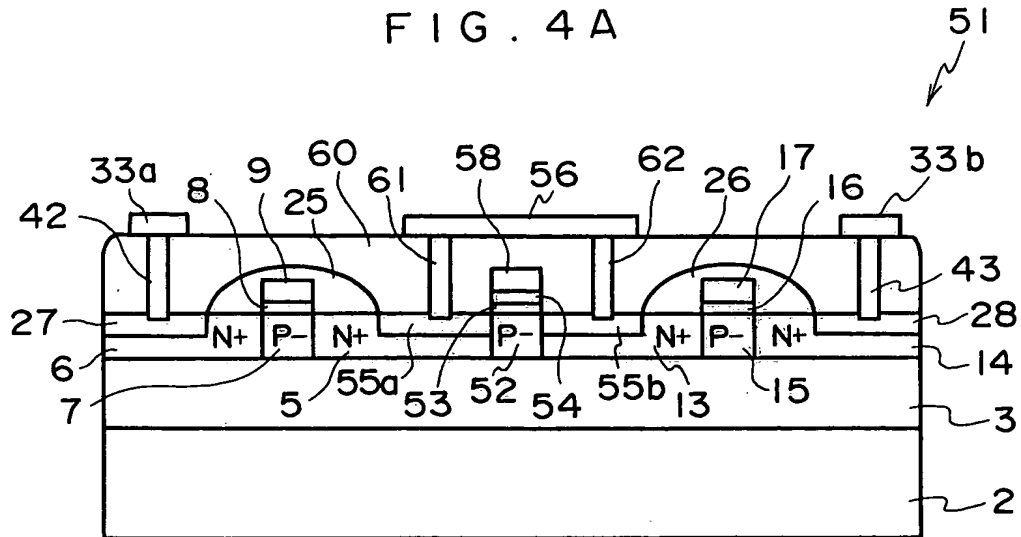


FIG. 4B

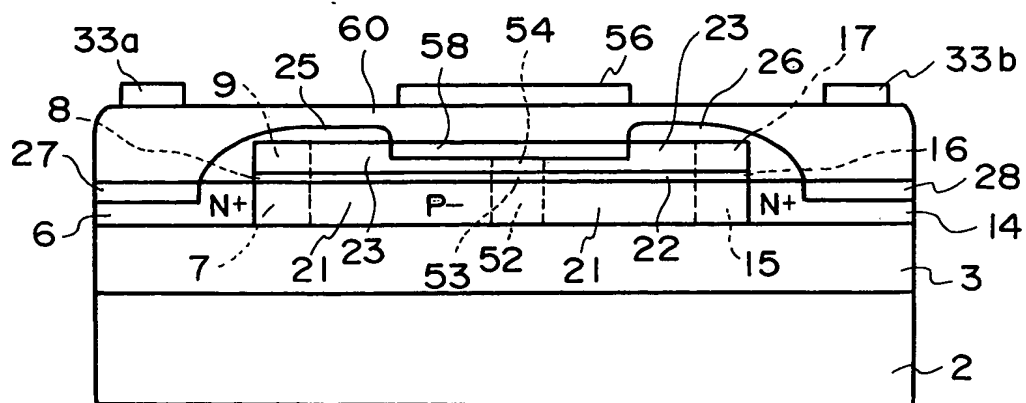


FIG. 5A

PRIOR ART

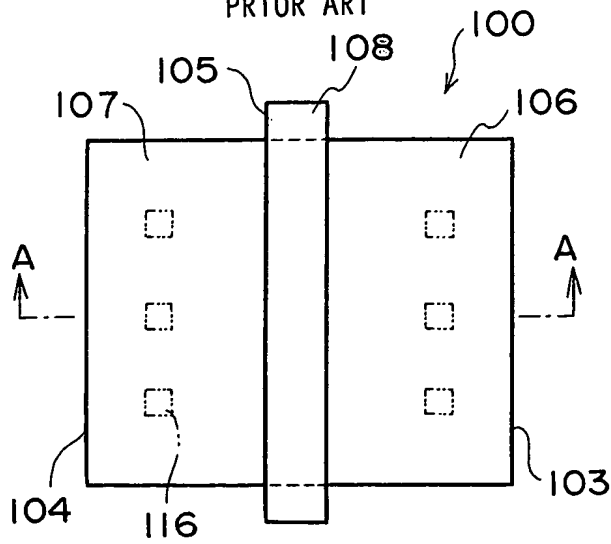


FIG. 5B

PRIOR ART

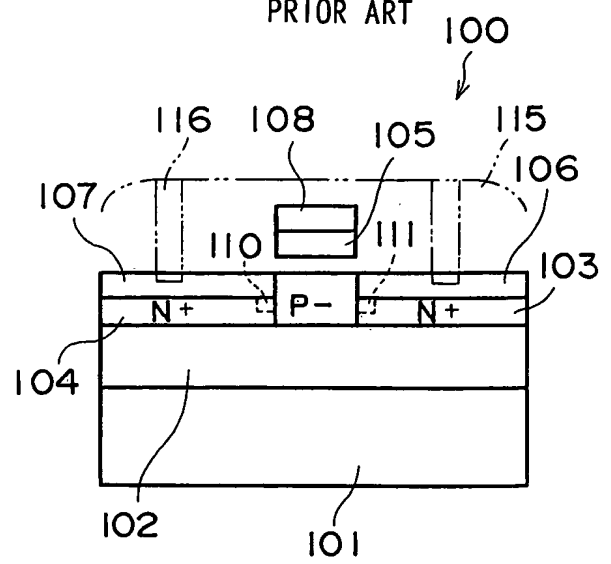


FIG. 6A

PRIOR ART

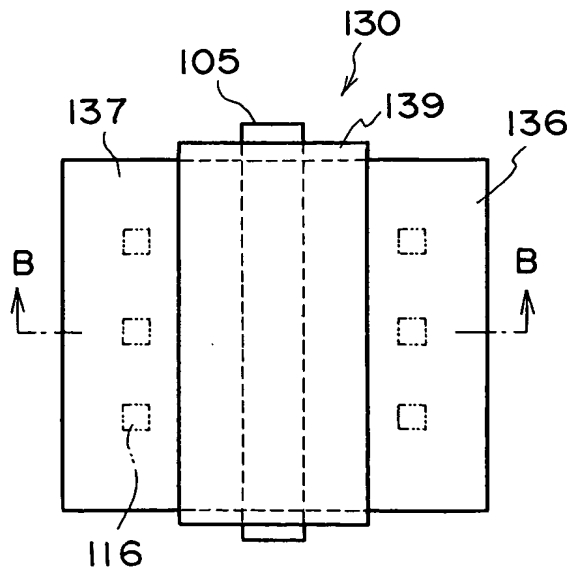


FIG. 6B

PRIOR ART

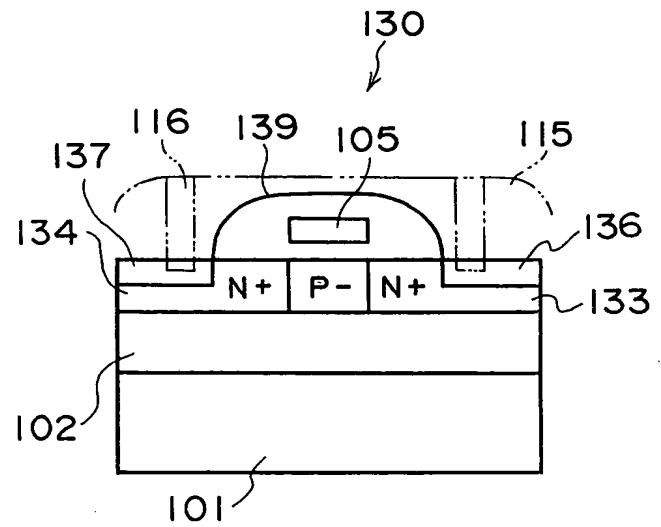


FIG. 7A PRIOR ART

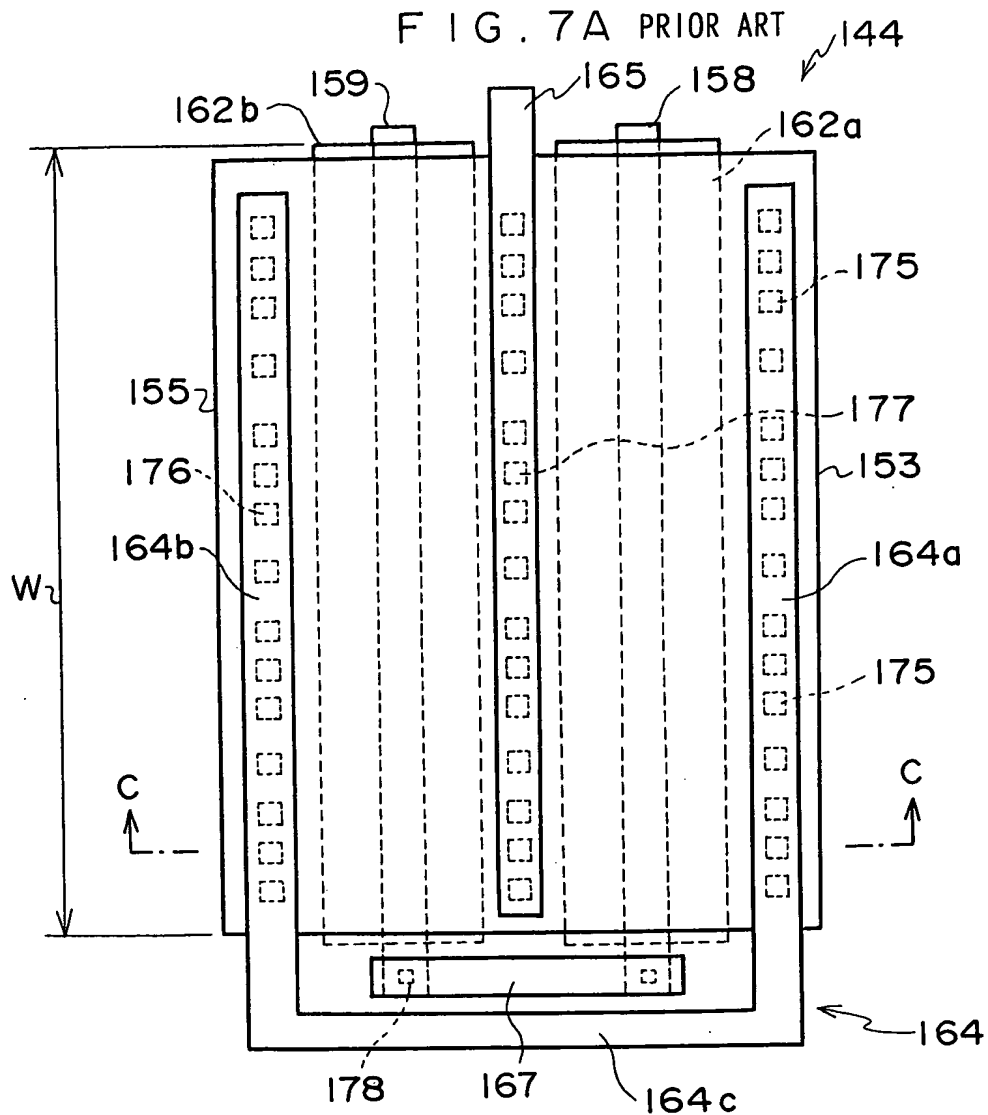


FIG. 7B PRIOR ART

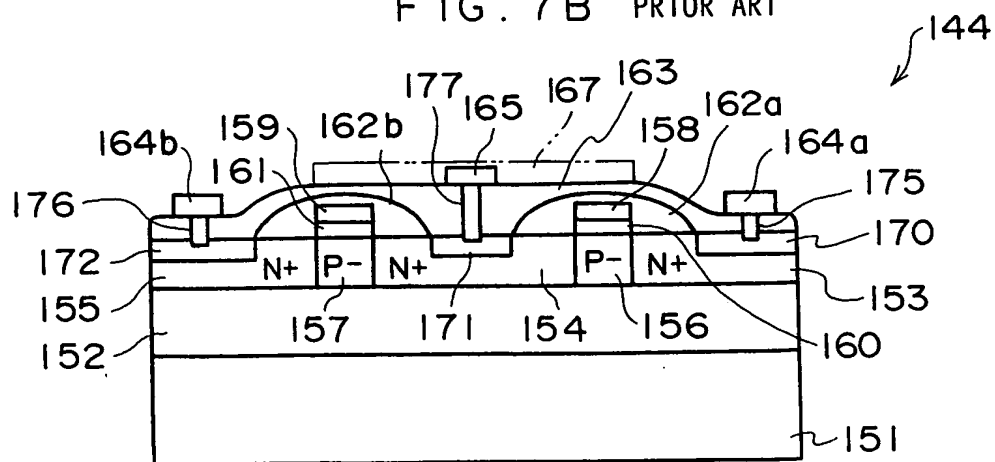


FIG. 8

PRIOR ART

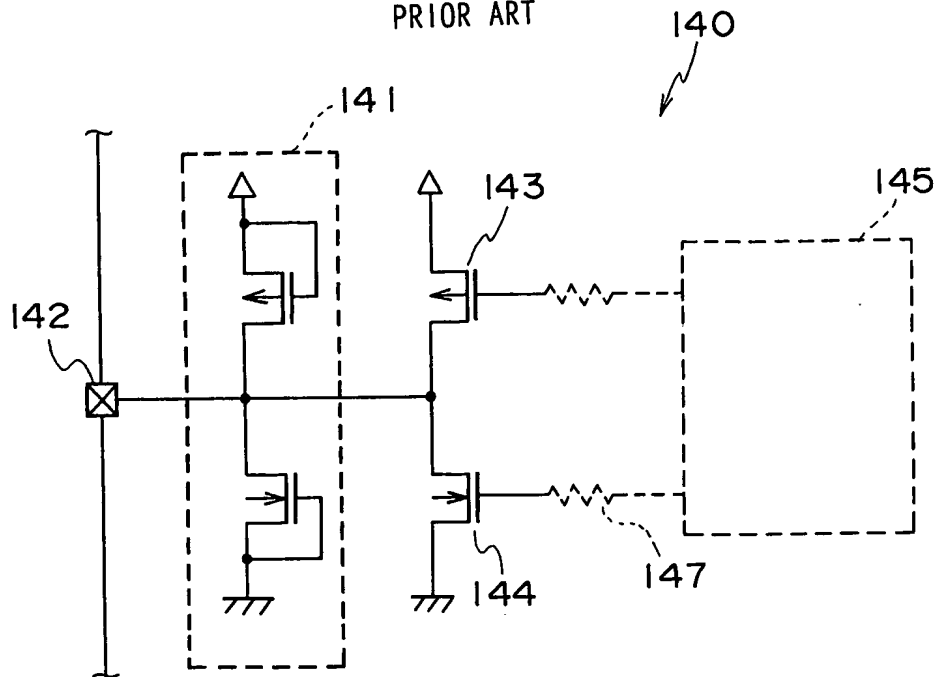


FIG. 9

